

## NCE N-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE0115K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

V<sub>DS</sub> =100V,I<sub>D</sub> =15A

 $R_{DS(ON)}$  < 100m $\Omega$  @  $V_{GS}$ =10V (Typ:80m $\Omega$ )

 $R_{DS(ON)} < 110 m\Omega @ V_{GS} = 4.5 V \quad (Typ:85 m\Omega)$ 

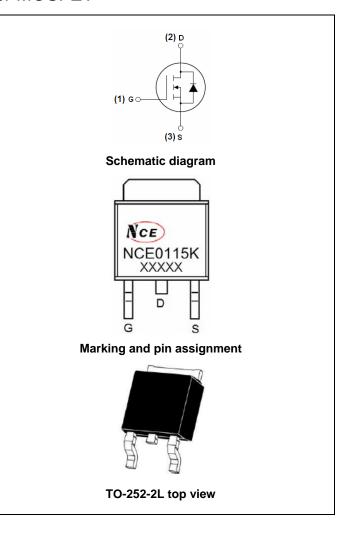
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

## **Application**

- Power switching application
- Hard switched and high frequency circuits

100% UIS TESTED!

100% AVds TESTED!



**Package Marking and Ordering Information** 

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0115K	NCE0115K	TO-252-2L	-	-	-

## Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	15	Α
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (100°C)	10.6	Α
Pulsed Drain Current	I <sub>DM</sub>	60	Α
Maximum Power Dissipation	P <sub>D</sub>	50	W
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	200	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^{\circ}\!\mathbb{C}$

#### **Thermal Characteristic**

Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	R <sub>eJC</sub>	3	°C/W
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	100	110	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.0	1.6	2.5	V
Drain Course On Ctata Desistance	Б	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	80	100	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	-	85	110	
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =10A	-	10	-	S
Dynamic Characteristics (Note4)	<u> </u>		•			
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V,	-	830	-	PF
Output Capacitance	Coss		-	44.2	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	30.1	-	PF
Switching Characteristics (Note 4)	l l					I
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}$ =50V, $R_L$ =6. 4 $\Omega$ $V_{GS}$ =10V, $R_G$ =3 $\Omega$	-	15	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	5	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	25	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =50V,I <sub>D</sub> =10A,	-	22.3		nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.87	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	6.14	-	nC
Drain-Source Diode Characteristics			,			1
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =15A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	15	Α

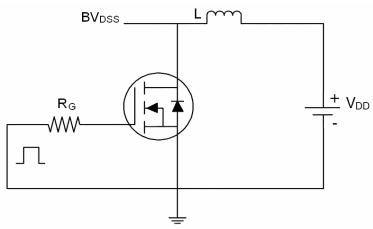
## Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature}.$
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=50V,VG=10V,L=0.5mH,Rg=25 $\Omega$

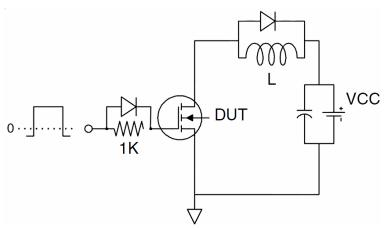


## **Test Circuit**

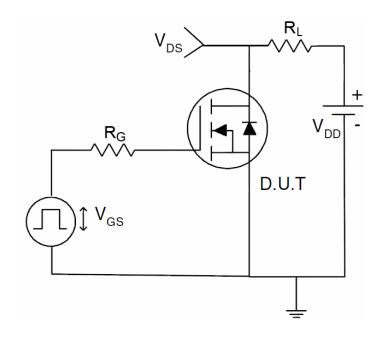
# 1) E<sub>AS</sub> test Circuit



# 2) Gate charge test Circuit

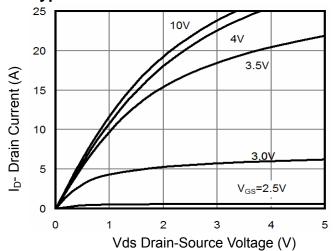


# 3) Switch Time Test Circuit

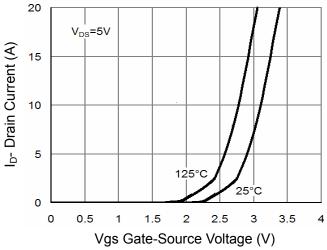








**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

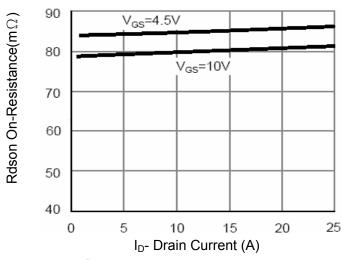


Figure 3 Rdson- Drain Current

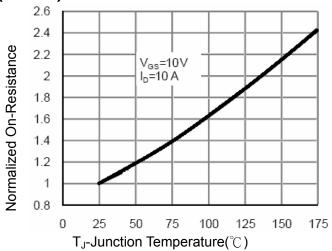


Figure 4 Rdson-JunctionTemperature

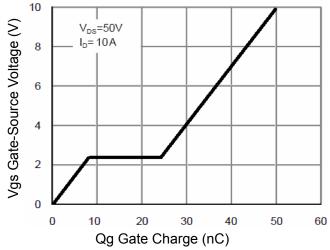


Figure 5 Gate Charge

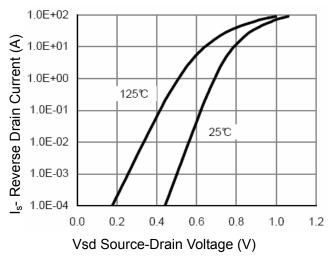


Figure 6 Source- Drain Diode Forward



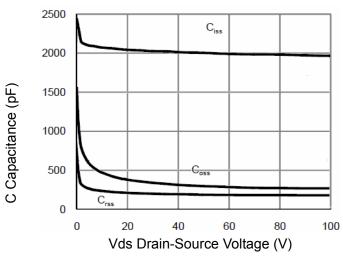
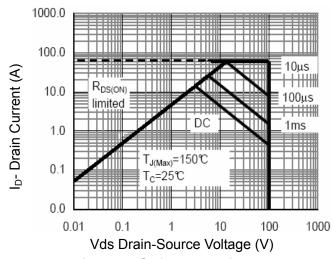


Figure 7 Capacitance vs Vds



**Figure 8 Safe Operation Area** 

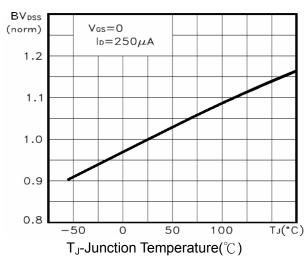


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

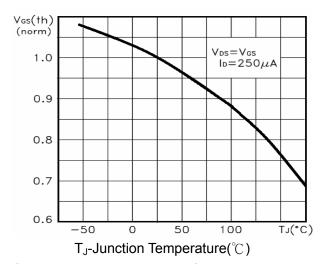
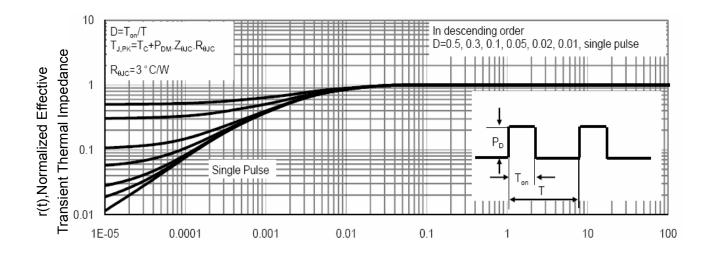


Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

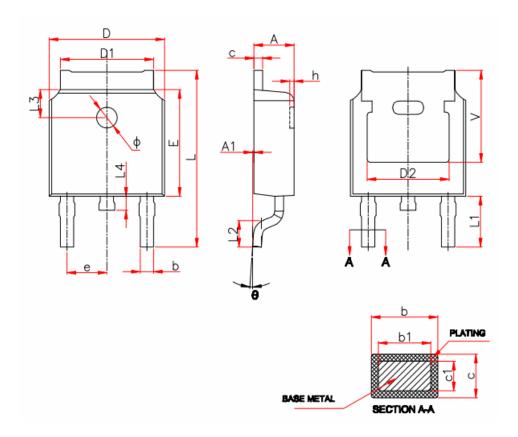


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



# **TO-252 Package Information**



Symbol	Millimeters			
Symbol	Min.	Max.		
Α	2.20	2.40		
A1	0.00	0.13		
b	0.66	0.86		
b1	0.73	0.79		
С	0.46	0.58		
c1	0.50	0.52		
D	6.50	6.70		
D1	5.10	5.46		
D2	4.83	REF.		
E	6.00	6.20		
е	2.19	2.39		
L	9.80	10.40		
L1	2.90 REF.			
L2	1.40	1.70		
L3	1.60 REF.			
L4	0.60	1.00		
Ф	1.10	1.30		
θ	0°	8°		





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